What is claimed is:

1. A gas supply assembly for providing a gas mixture comprising germanium tetrafluoride (GeF_4) and hydrogen (H_2) gases in an ion implantation chamber comprising:

one or more fluid supply package(s) comprising GeF_4 and H_2 wherein the assembly is configured to provide a gas mixture comprising GeF_4 and H_2 an ion implantation chamber, wherein H_2 is present in an amount in the range of 25%-67% (volume) of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 3:1 to 33:67.

2. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 37-67% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 63:37 to 33:67.

3. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 42-62% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 29:21 to 19:31

4. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 45-59% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 11:9 to 41:59

5. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 47-57% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 53:47 to 43:57.

6. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 49-55% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 51:49 to 9:11.

7. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 51-53% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 49:51 to 47:53.

8. The gas supply assembly of ~~any of the previous~~ claim~~s~~ 1, wherein the gases consist essentially of GeF_4 and H_2.

9. The gas supply assembly of ~~any of~~ claim~~s~~ 1~~-7~~, further comprising an inert gas selected from the group consisting of argon, helium, neon, nitrogen, xenon, and krypton.

10. The gas supply assembly of ~~any of~~ claim~~s~~ 1~~-7~~, wherein GeF_4 and H_2 are mixed in a single fluid supply package.

11. The gas supply assembly of ~~any of the~~ claim~~s~~ 1~~-7~~, wherein GeF_4 is present in a GeF_4-containing gas supply package and H_2 is present in a separate H_2-containing gas supply package.

12. The gas supply assembly of ~~any of~~ claim~~s~~ 1~~-7~~, wherein GeF_4 is not isotopically enriched.

13. A method of implanting germanium in a substrate, comprising introducing germanium tetrafluoride (GeF_4) and hydrogen (H_2) gases into an ion implantation chamber comprising, wherein introducing provides a gas mixture comprising GeF_4 and H_2 an ion implantation chamber, wherein H_2 is present in an amount in the range of 25%-67%, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 3:1 to 33:67.